

**April 2009** 

# MOC211M, MOC212M, MOC213M Small Ouline Optocouplers Transistor Output

### **Features**

- UL recognized (File #E90700, Volume 2)
- VDE recognized (File #136616) (add option 'V' for VDE approval, e.g., MOC211VM)
- Convenient plastic SOIC-8 surface mountable package style
- Standard SOIC-8 footprint, with 0.050" lead spacing
- Compatible with dual wave, vapor phase and IR reflow soldering
- High input-output isolation of 2500 V<sub>AC(rms)</sub> guaranteed
- Minimum BV<sub>CEO</sub> of 30V guaranteed

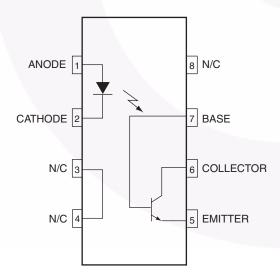
# **Applications**

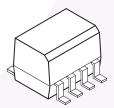
- General purpose switching circuits
- Interfacing and coupling systems of different potentials and impedances
- Regulation feedback circuits
- Monitor and detection circuits

# **Description**

These devices consist of a gallium arsenide infrared emitting diode optically coupled to a monolithic silicon phototransistor detector, in a surface mountable, small outline, plastic package. They are ideally suited for high density applications, and eliminate the need for throughthe-board mounting.

## **Schematic**





# **Absolute Maximum Ratings** (T<sub>A</sub> = 25°C Unless otherwise specified)

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Rating	Value	Unit	
EMITTER				
I <sub>F</sub>	Forward Current – Continuous	60	mA	
I <sub>F</sub> (pk)	Forward Current – Peak (PW = 100µs, 120pps)	1.0	А	
$V_{R}$	Reverse Voltage	6.0	V	
P <sub>D</sub>	LED Power Dissipation @ T <sub>A</sub> = 25°C	90	mW	
	Derate above 25°C	0.8	mW/°C	
DETECTOR				
V <sub>CEO</sub>	Collector-Emitter Voltage	-Emitter Voltage 30		
V <sub>ECO</sub>	Emitter-Collector Voltage	7.0	V	
V <sub>CBO</sub>	Collector-Base Voltage	70	V	
I <sub>C</sub>	Collector Current-Continuous	150	mA	
P <sub>D</sub>	Detector Power Dissipation @ T <sub>A</sub> = 25°C	150	mW	
	Derate above 25°C	1.76	mW/°C	
TOTAL DEVICE				
V <sub>ISO</sub>	Input-Output Isolation Voltage (f = 60Hz, t = 1 min.) <sup>(1)(2)(3)</sup>	2500	Vac(rms)	
$P_{D}$	Total Device Power Dissipation @ T <sub>A</sub> = 25°C	250	mW	
	Derate above 25°C	2.94	mW/°C	
T <sub>A</sub>	Ambient Operating Temperature Range	-40 to +100	°C	
T <sub>stg</sub>	Storage Temperature Range	-40 to +150	°C	
T <sub>L</sub>	Lead Soldering Temperature (1/16" from case, 10 sec. duration)	260	°C	

#### Notes:

- 1. Isolation Surge Voltage,  $V_{\text{ISO}}$ , is an internal device dielectric breakdown rating.
- 2. For this test, Pins 1 and 2 are common and Pins 5, 6 and 7 are common.
- 3.  $V_{ISO}$  rating of 2500  $V_{AC(rms)}$  for t = 1 min. is equivalent to a rating of 3,000  $V_{AC(rms)}$  for t = 1 sec.

# **Electrical Characteristics** ( $T_A = 25$ °C unless otherwise specified)

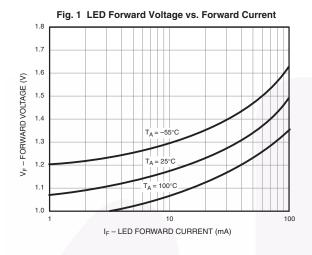
Symbol	Parameter	Test Conditions	Min.	Тур.*	Max.	Unit
EMITTER			1			
V <sub>F</sub>	Input Forward Voltage	I <sub>F</sub> = 10mA		1.15	1.5	V
I <sub>R</sub>	Reverse Leakage Current	V <sub>R</sub> = 6.0V		0.001	100	μΑ
C <sub>IN</sub>	Input Capacitance			18		pF
DETECTO	DR .		1	1		-
I <sub>CEO1</sub>	Collector-Emitter Dark Current	V <sub>CE</sub> = 10V, T <sub>A</sub> = 25°C V <sub>CE</sub> = 10V, T <sub>A</sub> = 100°C		1.0 1.0	50	nΑ μΑ
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 100μA	30	100		V
BV <sub>ECO</sub>	Emitter-Collector Breakdown Voltage	I <sub>E</sub> = 100μA	7.0	10		V
C <sub>CE</sub>	Collector-Emitter Capacitance	f = 1.0MHz, V <sub>CE</sub> = 0		7.0		pF
COUPLE	D		'	1		•
CTR	Collector-Output Current <sup>(4)</sup> MOC211M MOC212M MOC213M	I <sub>F</sub> = 10mA, V <sub>CE</sub> = 10V	20 50 100			%
V <sub>ISO</sub>	Isolation Surge Voltage <sup>(1)(2)(3)</sup>	f = 60 Hz AC Peak, t = 1 min.	2500			Vac(rms)
R <sub>ISO</sub>	Isolation Resistance <sup>(2)</sup>	V = 500V	10 <sup>11</sup>			Ω
V <sub>CE (sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 2.0mA, I <sub>F</sub> = 10mA			0.4	V
C <sub>ISO</sub>	Isolation Capacitance <sup>(2)</sup>	V = 0V, f = 1MHz		0.2		pF
t <sub>on</sub>	Turn-On Time	$I_C = 2.0$ mA, $V_{CC} = 10$ V, $R_L = 100\Omega$ (Fig. 10)		7.5		μs
t <sub>off</sub>	Turn-Off Time	$I_C = 2.0$ mA, $V_{CC} = 10$ V, $R_L = 100\Omega$ (Fig. 10)		5.7		μs
t <sub>r</sub>	Rise Time	$I_C = 2.0$ mA, $V_{CC} = 10$ V, $R_L = 100\Omega$ (Fig. 10)		3.2		μs
t <sub>f</sub>	Fall Time	$I_C = 2.0$ mA, $V_{CC} = 10$ V, $R_L = 100\Omega$ (Fig. 10)		4.7		μs

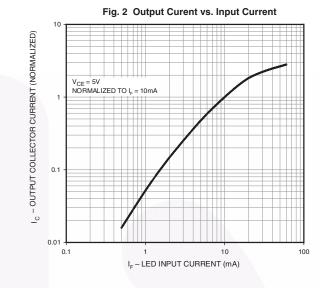
<sup>\*</sup>Typical values at  $T_A = 25$ °C

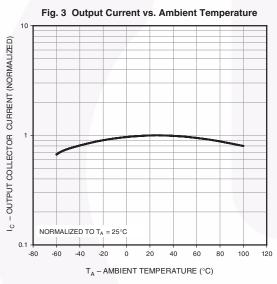
#### Notes:

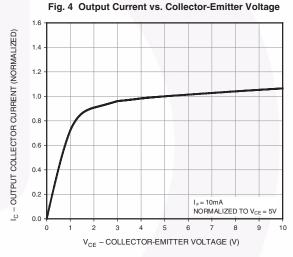
- 1. Isolation Surge Voltage,  $V_{\mbox{\scriptsize ISO}}$ , is an internal device dielectric breakdown rating.
- 2. For this test, Pins 1 and 2 are common and Pins 5, 6 and 7 are common.
- 3.  $V_{ISO}$  rating of 2500  $V_{AC(rms)}$  for t = 1 min. is equivalent to a rating of 3,000  $V_{AC(rms)}$  for t = 1 sec.
- 4. Current Transfer Ratio (CTR) =  $I_C/I_F \times 100\%$ .

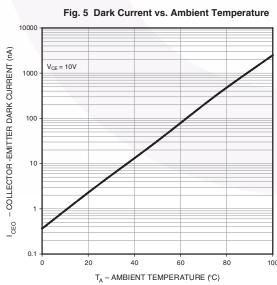
# **Typical Performance Curves**

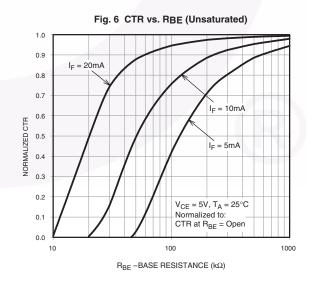




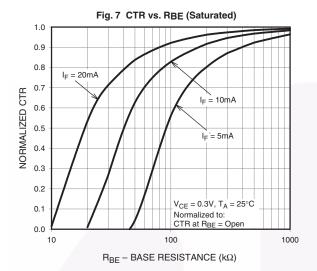








# Typical Performance Curves (Continued)



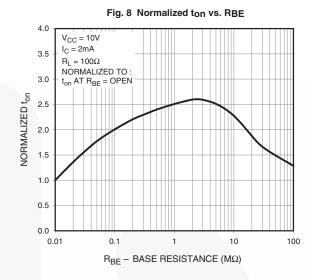


Fig. 9 Normalized toff vs. RBE 1.6 V<sub>CC</sub> = 10V  $I_C = 2mA$ 1.4  $R_L = 100\Omega$ NORMALIZED TO : t<sub>off</sub> AT R<sub>BE</sub> = OPEN NORMALIZED toff 1.0 0.8 0.6 0.2 0.0 10 0.01 100  $R_{BE}$  – BASE RESISTANCE (M $\Omega$ )

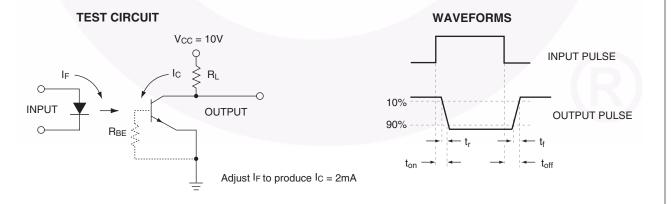
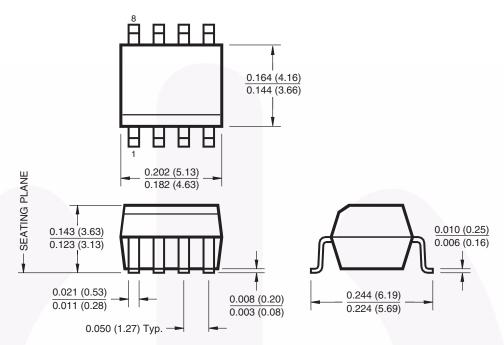


Figure 10. Switching Time Test Circuit and Waveforms

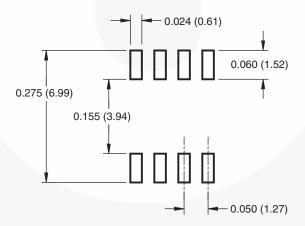
## **Package Dimensions**

## 8-pin SOIC Surface Mount



Lead Coplanarity: 0.004 (0.10) MAX

## **Recommended Pad Layout**



Dimensions in inches (mm).

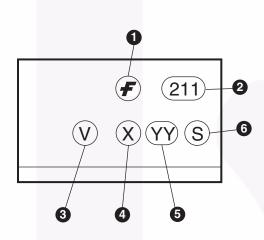
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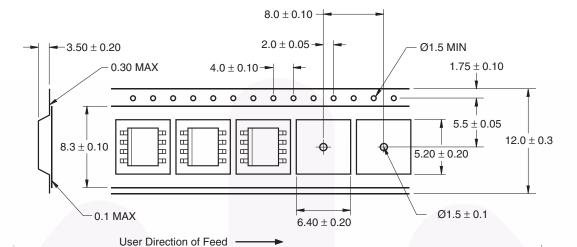
Option	Order Entry Identifier	Description
V	V	VDE 0884
R2	R2	Tape and reel (2500 units per reel)
R2V	R2V	VDE 0884, Tape and reel (2500 units per reel)

# **Marking Information**



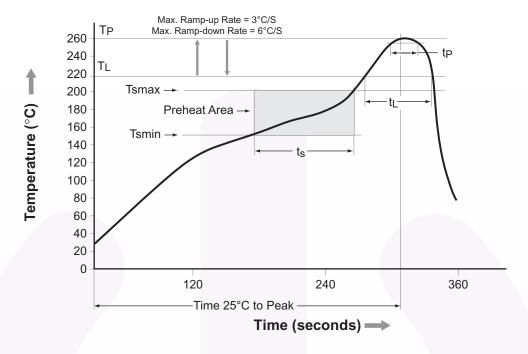
Defini	tions	
1	Fairchild logo	
2	Device number	
3	VDE mark (Note: Only appears on parts ordered with VDE option – See order entry table)	
4	One digit year code, e.g., '8'	
5	Two digit work week ranging from '01' to '53'	
6	Assembly package code	

# **Carrier Tape Specifications**



Dimensions in mm

## **Reflow Profile**



Profile Freature	Pb-Free Assembly Profile	
Temperature Min. (Tsmin)	150°C	
Temperature Max. (Tsmax)	200°C	
Time (t <sub>S</sub> ) from (Tsmin to Tsmax)	60-120 seconds	
Ramp-up Rate (t <sub>L</sub> to t <sub>P</sub> )	3°C/second max.	
Liquidous Temperature (T <sub>L</sub> )	217°C	
Time (t <sub>L</sub> ) Maintained Above (T <sub>L</sub> )	60-150 seconds	
Peak Body Package Temperature	260°C +0°C / -5°C	
Time (t <sub>P</sub> ) within 5°C of 260°C	30 seconds	
Ramp-down Rate (T <sub>P</sub> to T <sub>L</sub> )	6°C/second max.	
Time 25°C to Peak Temperature	8 minutes max.	





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